

## BTA24/BTB24

双向可控硅  
TRIAC

版本号  
201603-A

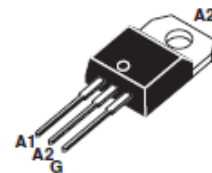
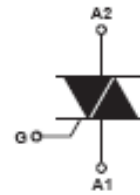
### 产品概述 GENERAL DESCRIPTION

BTA/BTB24 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

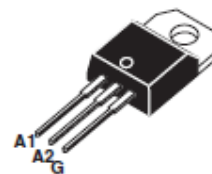
BTA/BTB24 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

### 主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	20	A
$V_{DRM}/V_{RRM}$	600&800	V
$I_{GT}$	$\leq 50$	mA



TO-220AB



TO-220E

### 产品特性

### FEATURES

- dv/dt高
- 通态压降低
- Rohs环保产品
- Highly dv/dt
- Low on-state voltage
- Rohs Products

### 应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

**极限值(除非另有规定,  $T_j=25^\circ\text{C}$ ) ABSOLUTE RATINGS**

 ( $T_j=25^\circ\text{C}$ , unless otherwise specified)

符号 Symbol	参数 Parameter		数值 Value	单位 Unit
$I_{T(RMS)}$	RMS 通态电流 RMS on-state current (full sine wave)	$T_C=105^\circ\text{C}$	20	A
$I_{TSM}$	通态峰值浪涌电流 Non repetitive surge peak on-state current	$F=50\text{Hz}, t=20\text{ms}$	210	A
$I^2t$	$I^2t$ 耗散值 $I^2t$ value for fusing	$T_p=10\text{ms}$	200	$\text{A}^2\text{s}$
di/dt	通态电流上升值 Critical rate of rise of on-state current	$F=120\text{Hz}, T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
$I_{GM}$	门极峰值电流 Peak gate current	$T_p=20\mu\text{s}, T_j=125^\circ\text{C}$	4	A
$P_{G(AV)}$	平均门极耗散功率 Average gate power dissipation	$T_j=125^\circ\text{C}$	1	W
Tstg	贮存结温范围 Storage junction temperature range		-40+150	$^\circ\text{C}$
$T_j$	工作结温范围 Operating junction temperature range		-40+125	$^\circ\text{C}$

**电参数(除非另有规定,  $T_j=25^\circ\text{C}$ ) ELECTRICAL CHARACTERISTICS**

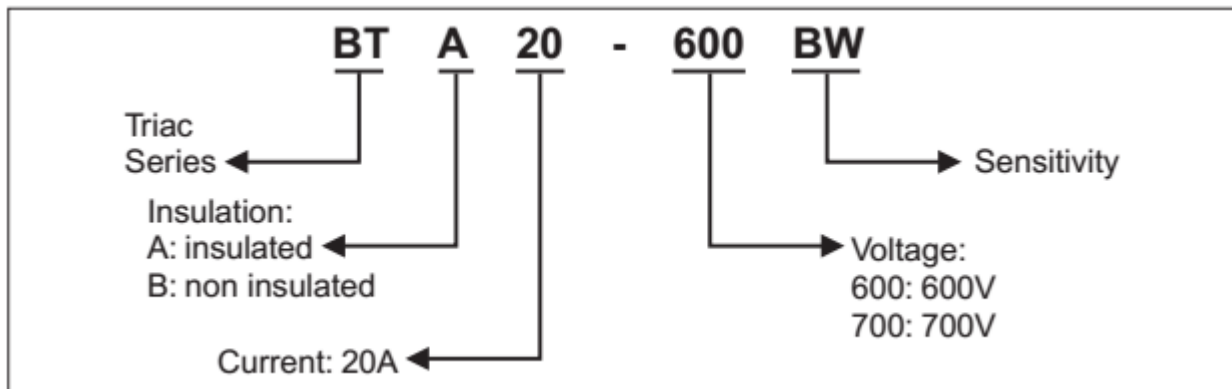
 ( $T_j=25^\circ\text{C}$ , unless otherwise specified)

参数 Parameter	符号 Symbol		规范值 Value		单位 Unit	测试条件 Test Conditions
			CW	BW		
触发电流 Gate trigger current	$I_{GT}$	I ~ III	$\leq 35$	$\leq 50$	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
触发电压 Gate trigger voltage	$V_{GT}$	I ~ III	$\leq 1.5$		V	$V_D=12\text{V}, I_T=0.1\text{A}$
维持电流 Holding current	$I_H$		$\leq 50$	$\leq 75$	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
擎住电流 Latching current	$I_L$		$\leq 80$	$\leq 100$	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
电压上升率 Rise of off- state voltage	dv/dt		$\geq 200$	$\geq 500$	$\text{V}/\mu\text{s}$	$V_D=67\% V_{DRM}$
通态压降 Peak on-state voltage	$V_{TM}$		$\leq 1.7$		V	$I_T=28\text{A}$
断态漏电流 Peak repetitive forward blocking current	$I_{DRM}$		$\leq 10$		$\mu\text{A}$	$V_{RRM}=V_{DRM}, T_j=25^\circ\text{C}$
	$I_{RRM}$		$\leq 3$		mA	$V_{RRM}=V_{DRM}, T_j=125^\circ\text{C}$

## 热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
Rth(j-c)	Junction to case(AC)	TO-220AB	0.8
		TO-220E	1.7
Rth(j-a)	Junction to ambient	TO-220AB	60
		TO-220E	60

## ORDERING INFORMATION



**特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)**

图1 最大耗散功率与RMS通态电流关系  
Fig.1.Maximum Power Dissipation Versus on-state current

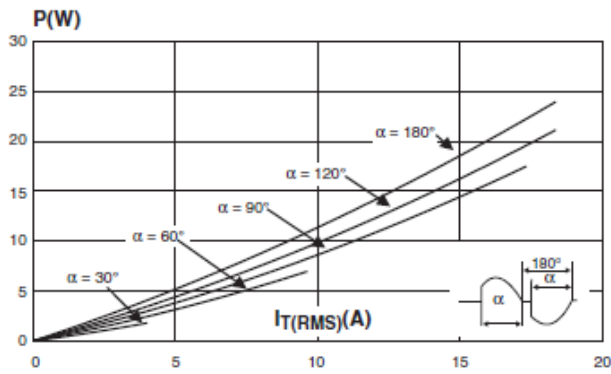


图2 RMS通态电流与Tc温度关系  
Fig.2. RMS On-state Current Versus TL

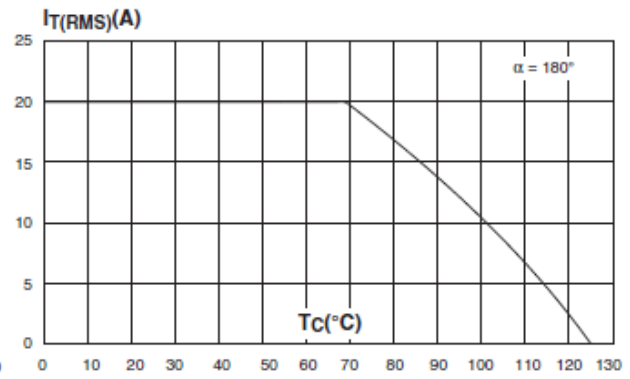


图3 通态特性  
Fig.3.On-State Characteristics

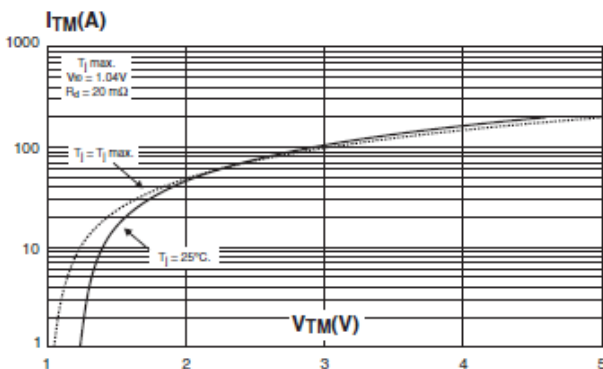


图4 通态浪涌峰值电流与周期数关系  
Fig.4.Surge Peak On-state Current Versus Number Cycles

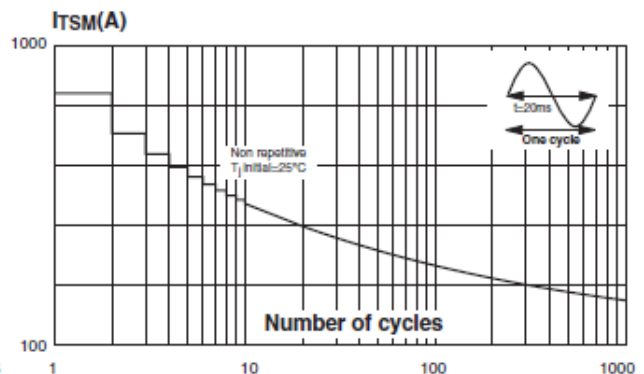
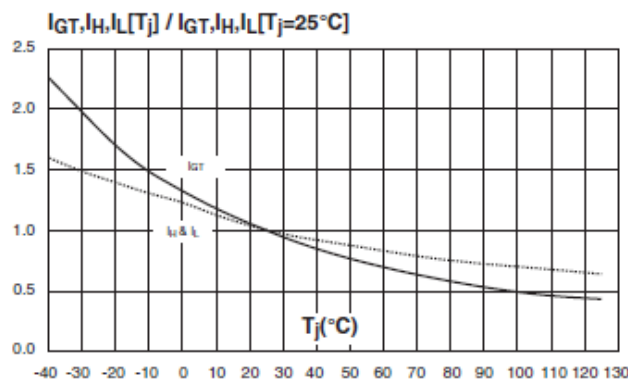


图5  $I_{GT}$ 、 $I_H$ 、 $I_L$ 相对值（相对于 $25^\circ\text{C}$ ）与结温关系  
Fig.5.Relative Variation Of Gate Trigger Current , Holding Current And Latching Current Versus Junction Temperature (Typical Value)



**封装尺寸 PACKAGE MECHANICAL DATA**

**TO-220AB AND TO-220E**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.40		0.70	0.015		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.70	0.244		0.264
ØI	3.70		3.85	0.146		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

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